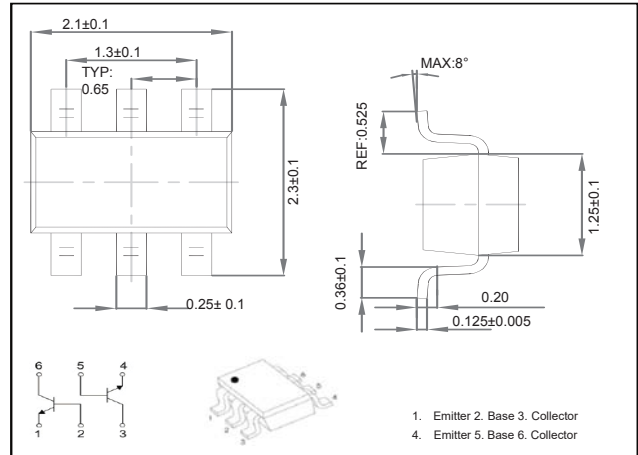


**SOT-363 Plastic-Encapsulate Transistors**
**Features**

- Epitaxial Planar Die Construction
- Ideal for Low power Amplification and Switching
- High Stability and High Reliability

**Mechanical Data**

- SOT-363 Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any


**MAXIMUM RATINGS AND CHARACTERISTICS @**

25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	40	V
Emitter -Base Voltage	VEBO	6	V
Collector Current-Continuous	IC	600	mA
Collector Power Dissipation	PC	200	mW
Thermal Resistance from Junction to Ambient	RθJA	625	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55-+150	°C

**Electrical Specification(T<sub>A</sub>=25°C unless otherwise specified)**

Parameter	Symbols	Test Condition	Limits		Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	IC=100uA, IE=0	60		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=1mA, IB=0	40		V
Emitter-base breakdown voltage	V(BR)EBO	IE=100uA, IC=0	6		V
Collector cut-off current	ICBO	VCB=50V, IE=0		100	nA
Collector cut-off current	ICEO	VCE=35V, IB=0		500	nA
Emitter cut-off current	IEBO	VEB=5V, IC=0		100	nA
DC current gain	hFE(1)*	VCE=1V, IC=0.1mA	20		
	hFE(2)*	VCE=1V, IC=1mA	40		
	hFE(3)*	VCE=1V, IC=10mA	80		
	hFE(4)*	VCE=1V, IC=150mA	100	300	
	hFE(5)*	VCE=2V, IC=500mA	40		
Collector-emitter saturation voltage	VCE(sat)*	IC=500mA, IB=50mA		0.75	V
		IC=150mA, IB=15mA		0.40	V
Base -emitter saturation voltage	VBE(sat)*	IC=500mA, IB=50mA		1.20	V
		IC=150mA, IB=15mA	0.75	0.95	V
Transition frequency	FT	VCE=10V, IC=20mA, f=100MHz	250		MHz
Output Capacitance	Cob	VCB=5V, IE=0, f=1MHz		6.5	pF
Delay time	td	VCC=30V, VBE(off)=2V, IC=150mA, IB1=15mA		15	Ns
Rise time	tr			20	Ns
Storage time	ts			225	Ns
Fall time	tf	VCC=30V, IC=150mA, IB1=IB2=15mA		30	ns

\* Pulse test: pulse width≤300us, duty cycles≤2.0%.

## Typical characteristics

